

Abstract Submitted
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Experimental investigation of plasma parameter profiles on wafer level with discharge gap lengths in an inductively coupled plasma JU HO KIM, Department of Electrical Engineering, Hanyang University, Seoul, 133-791, Republic of Korea, YOUNG-CHEOL KIM, JUNE YOUNG KIM, Department of Nanoscale Semiconductor Engineering, Hanyang University, Seoul 133-791, South Korea, CHIN-WOOK CHUNG, Department of Electrical Engineering, Hanyang University, Seoul, 133-791, Republic of Korea — Experimental investigation of the gap length effect on plasma parameters was performed in a planar type inductively coupled plasma (ICP) at various conditions. The spatial profile (wafer level, 260 mm) of ion flux, and electron temperature were measured from a 2-D floating probe measurement system. At low pressures, the spatial profile of the ion flux rarely changed; however, at relatively high pressures, the spatial profile of the ion flux dramatically changed with different discharge gap length.

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